1-of-8 **Decoder/Demultiplexer**

The MC74AC138/74ACT138 is a high-speed 1-of-8 decoder/demultiplexer. This device is ideally suited for high-speed bipolar memory chip select address decoding.

The multiple input enables allow parallel expansion to a 1–of–24 decoder using just three MC74AC138/74ACT138 devices or a 1–of–32 decoder using four MC74AC138/74ACT138 devices and one inverter.

- Demultiplexing Capability
- Multiple Input Enable for Easy Expansion
- Active LOW Mutually Exclusive Outputs
- Outputs Source/Sink 24 mA
- 'ACT138 Has TTL Compatible Inputs
- These are Pb-Free Devices

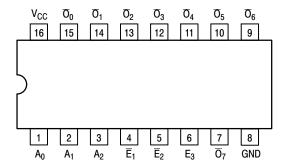


Figure 1. Pinout: 16-Lead Packages Conductors (Top View)

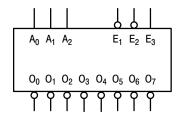


Figure 2. Logic Symbol

PIN ASSIGNMENT

PIN	FUNCTION
A ₀ -A ₂	Address Inputs
\overline{E}_1 – \overline{E}_2	Enable Inputs
E ₃	Enable Input
\overline{O}_0 – \overline{O}_7	Outputs



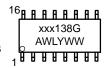
ON Semiconductor™

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MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



xxx = AC or ACT

A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

FUNCTIONAL DESCRIPTION

The MC74AC138/74ACT138 high–speed 1–of–8 decoder/demultiplexer accepts three binary weighted inputs (A₀, A₁, A₂) and, when enabled, provides eight mutually exclusive active–LOW outputs (\overline{O}_0 – \overline{O}_7). The MC74AC138/74ACT138 features three Enable inputs, two active–LOW (\overline{E}_1 , \overline{E}_2) and one active–HIGH (E₃). All outputs will be HIGH unless \overline{E}_1 and \overline{E}_2 are LOW and E₃ is

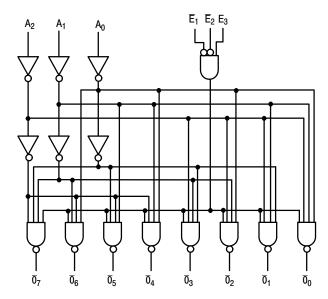
HIGH. This multiple enabled function allows easy parallel expansion of the device to a 1–of–32 (5 lines to 32 lines) decoder with just four MC74AC138/74ACT138 devices and one inverter (See Figure 4). The MC74AC138/74ACT138 can be used as an 8–output demultiplexer by using one of the active LOW Enable inputs as the data input and the other Enable inputs as strobes. The Enable inputs which are not used must be permanently tied to their appropriate active–HIGH or active–LOW state.

TRUTH TABLE

		Inp	uts						Out	outs			
E ₁	\overline{E}_2	E ₃	A ₀	A ₁	A ₂	\overline{O}_0	\overline{O}_1	\overline{O}_2	\overline{O}_3	\overline{O}_4	\overline{O}_5	\overline{O}_6	\overline{O}_7
Н	Χ	Χ	Χ	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
Х	Н	Х	Χ	Х	X	Н	Н	Н	Н	Н	Н	Н	Н
Х	Χ	L	Χ	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
L	L	Н	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
L	L	Н	Н	L	L	Н	L	Н	Н	Н	Н	Н	Н
L	L	Н	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н
L	L	Н	Н	Н	L	Н	Н	Н	L	Н	Н	Н	Н
L	L	Н	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н
L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н
L	L	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	L	Н
L	L	Н	Η	Н	Н	Н	Н	Н	Η	Η	Н	Н	L

H = HIGH Voltage Level L = LOW Voltage Level

X = Immaterial



NOTE: This diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Figure 3. Logic Diagram

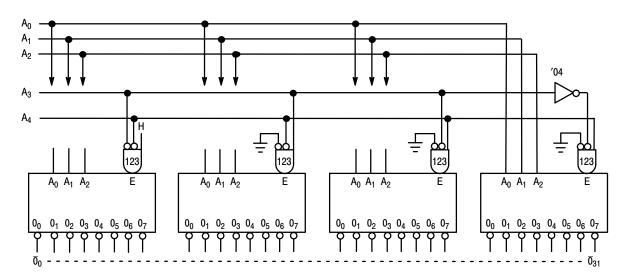


Figure 4. Expansion to 1-of-32 Decoding

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit			
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V			
VI	DC Input Voltage		$-0.5 \le V_{I} \le V_{CC} + 0.5$	V			
Vo	DC Output Voltage	(Note 1)	$-0.5 \le V_{O} \le V_{CC} + 0.5$	V			
I _{IK}	DC Input Diode Current		±20	mA			
lok	DC Output Diode Current		±50	mA			
Io	DC Output Sink/Source Current		±50	mA			
I _{CC}	DC Supply Current per Output Pin		±50				
I _{GND}	DC Ground Current per Output Pin		±50				
T _{STG}	Storage Temperature Range		-65 to +150	°C			
TL	Lead temperature, 1 mm from Case for 10 Seconds		260	°C			
TJ	Junction temperature under Bias		+150	°C			
θ_{JA}	Thermal Resistance (Note 2)	SOIC TSSOP	69.1 103.8	°C/W			
P _D	Power Dissipation in Still Air at 65°C (Note 3)	SOIC TSSOP	500 500	mW			
MSL	Moisture Sensitivity		Level 1				
F _R	Flammability Rating Oxygen	Index: 30% – 35%	UL 94 V-0 @ 0.125 in				
V _{ESD}	Machi	ndy Model (Note 4) ine Model (Note 5) ice Model (Note 6)	> 2000 > 200 > 1000	V			
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GNI	D at 85°C (Note 7)	±100	mA			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Io absolute maximum rating must be observed.
- 2. The package thermal impedance is calculated in accordance with JESD51–7.
- 3. 500 mW at 65°C; derate to 300 mW by 10 mW/ from 65°C to 85°C.
- 4. Tested to EIA/JESD22-A114-A.
- 5. Tested to EIA/JESD22-A115-A.
- 6. Tested to JESD22-C101-A.
- 7. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit	
	0 1 1 1 1	'AC	2.0	5.0	6.0	.,	
V _{CC}	Supply Voltage	'ACT	4.5	5.0	5.5	V	
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Ref. to GND)		0	-	V _{CC}	V	
		V _{CC} @ 3.0 V	-	150	-		
t _r , t _f	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V _{CC} @ 4.5 V	-	40	-	ns/V	
	No Devices except commit inputs	V _{CC} @ 5.5 V	_	25	-		
	Input Rise and Fall Time (Note 2)	V _{CC} @ 4.5 V	_	10	-	0 /	
t _r , t _f	'ACT Devices except Schmitt Inputs	V _{CC} @ 5.5 V	_	8.0	-	ns/V	
TJ	Junction Temperature (PDIP)		_	-	140	°C	
T _A	Operating Ambient Temperature Range	-40	25	85	°C		
I _{OH}	Output Current – High	-	-	-24	mA		
I _{OL}	Output Current – Low		-	-	24	mA	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- V_{IN} from 30% to 70% V_{CC}; see individual Data Sheets for devices that differ from the typical input rise and fall times.
 V_{IN} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

			74.	AC	74AC			
Symbol	Parameter	V _{CC} (V)	T _A =	+25°C	T _A = -40°C to +85°C	Unit	Conditions	
			Тур	Gua	aranteed Limits			
V _{IH}	Minimum High Level Input Voltage		1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I _{OUT} = -50 μA	
		3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	٧	*V _{IN} = V _{IL} or V _{IH} -12 mA I _{OH} -24 mA -24 mA	
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	I _{OUT} = 50 μA	
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	*V _{IN} = V _{IL} or V _{IH} 12 mA I _{OL} 24 mA 24 mA	
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	V _I = V _{CC} , GND	
I _{OLD}	†Minimum Dynamic	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max	
I _{OHD}	Output Current	5.5	_	-	-75	mA	V _{OHD} = 3.85 V Min	
I _{CC}	Maximum Quiescent Supply Current	5.5	_	8.0	80	μА	V _{IN} = V _{CC} or GND	

 $^{^\}star\text{All}$ outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

NOTE: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V_{CC} .

AC CHARACTERISTICS

			74AC T _A = +25°C C _L = 50 pF			74	AC		
Symbol	Parameter	V _{CC} * (V)				T _A = -40°C C _L = 9		Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay A _n to Ō _n	3.3 5.0	1.5 1.5	8.5 6.5	13.0 9.5	1.5 1.5	15.0 10.5	ns	3–6
t _{PHL}	Propagation Delay A _n to Ō _n	3.3 5.0	1.5 1.5	8.0 6.0	12.5 9.0	1.5 1.5	14.0 10.5	ns	3–6
t _{PLH}	Propagation Delay \overline{E}_1 or \overline{E}_2 to \overline{O}_n	3.3 5.0	1.5 1.5	11.0 8.0	15.0 11.0	1.5 1.5	16.0 12.0	ns	3–6
t _{PHL}	Propagation Delay \overline{E}_1 or \overline{E}_2 to \overline{O}_n	3.3 5.0	1.5 1.5	9.5 7.0	13.5 9.5	1.5 1.5	15.0 10.5	ns	3–6
t _{PLH}	Propagation Delay E_3 to \overline{O}_n	3.3 5.0	1.5 1.5	11.0 8.0	15.5 11.0	1.5 1.5	16.5 12.5	ns	3–6
t _{PHL}	Propagation Delay E_3 to \overline{O}_n	3.3 5.0	1.5 1.5	8.5 6.0	13.0 8.0	1.5 1.0	14.0 9.5	ns	3–6

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V. *Voltage Range 5.0 V is 5.0 V ± 0.5 V.

DC CHARACTERISTICS

			74 <i>A</i>	CT	74ACT		
Symbol	Parameter	V _{CC} (V)	T _A = -	+25°C	T _A = -40°C to +85°C	Unit	Conditions
			Тур	Gua	ranteed Limits		
V _{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V
V _{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V	I _{OUT} = -50 μA
		4.5 5.5	_ _	3.86 4.86	3.76 4.76	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ $^{-24} \text{ mA}$ ^{1}OH $^{-24} \text{ mA}$
V _{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V	I _{OUT} = 50 μA
		4.5 5.5	_ _	0.36 0.36	0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ $^{24} \text{ mA}$ ^{1}OL $^{24} \text{ mA}$
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	$V_I = V_{CC}$, GND
ΔI_{CCT}	Additional Max. I _{CC} /Input	5.5	0.6	-	1.5	mA	$V_{I} = V_{CC} - 2.1 \text{ V}$
I _{OLD}	†Minimum Dynamic	5.5	-	_	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}	Output Current	5.5	-	_	- 75	mA	V _{OHD} = 3.85 V Min
Icc	Maximum Quiescent Supply Current	5.5	-	8.0	80	μΑ	V _{IN} = V _{CC} or GND

^{*}All outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS

			74ACT T _A = +25°C C _L = 50 pF			74ACT			
Symbol	Parameter	V _{CC} * (V)				T _A = -40°C C _L = 5		Unit	Fig. No.
			Min	Тур	Max	Min	Max		
t _{PLH}	Propagation Delay A_n to \overline{O}_n	5.0	1.5	7.0	10.5	1.5	11.5	ns	3–6
t _{PHL}	Propagation Delay A_n to \overline{O}_n	5.0	1.5	6.5	10.5	1.5	11.5	ns	3–6
t _{PLH}	Propagation Delay \overline{E}_1 or \overline{E}_2 to \overline{O}_n	5.0	2.5	8.0	11.5	2.0	12.5	ns	3–6
t _{PHL}	Propagation Delay \overline{E}_1 or \overline{E}_2 to \overline{O}_n	5.0	2.0	7.5	11.5	2.0	12.5	ns	3–6
t _{PLH}	Propagation Delay E _{3 to} \overline{O}_{n}	5.0	2.5	8.0	12.0	2.0	13.0	ns	3–6
t _{PHL}	Propagation Delay E_3 to \overline{O}_n	5.0	2.0	6.5	10.5	1.5	11.5	ns	3–6

^{*}Voltage Range 5.0 V is 5.0 V $\pm\,0.5$ V

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	60	pF	V _{CC} = 5.0 V

ORDERING INFORMATION

Device Order Number	Package	Shipping [†]
MC74AC138DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74AC138DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74AC138DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel
MC74ACT138DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74ACT138DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74ACT138DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES		
DIM	MIN	MAX	MIN	MAX		
Α	9.80	10.00	0.386	0.393		
В	3.80	4.00	0.150	0.157		
C	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.050 BSC			
J	0.19	0.25	0.008	0.009		
K	0.10	0.25	0.004	0.009		
M	0°	7°	0°	7°		
P	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION		BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.		7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	OOL DEDING	COOTDONT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		i.40 — →
								- 0	.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				10% 1.12
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	Τ\		1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			, L .	'0
3. 4.	DRAIN, #2	3. 4.	CATHODE	3. 4.	GATE P-CH	1)		- —	
4. 5.	DRAIN, #2	4. 5.	CATHODE	4. 5.	COMMON DRAIN (OUTPU	Τ\		, , , , , , , , , , , , , , , , , , , 	
5. 6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		16	5X 1 -	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.5	58	, L
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	•,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.		12.	COMMON DRAIN (OUTPU				
13.	GATE, #2	13.		13.	GATE N-CH	.,			
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPU	T)			V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				1 <u>+=</u> 1- 1
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	.,			
								□ 8	9 + - + -
									~
									' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '
									DIMENSIONS: MILLIMETERS

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DESCRIPTION:	SOIC-16		PAGE 1 OF 1	

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☐ 0.10 (0.004)

D

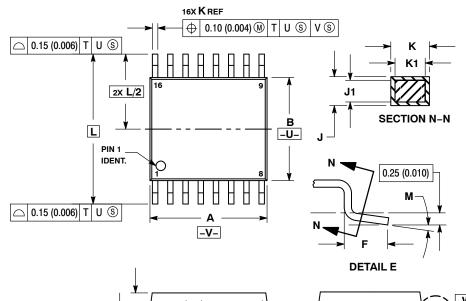
-T- SEATING PLANE





TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ы	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	TSSOP-16		PAGE 1 OF 1	

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